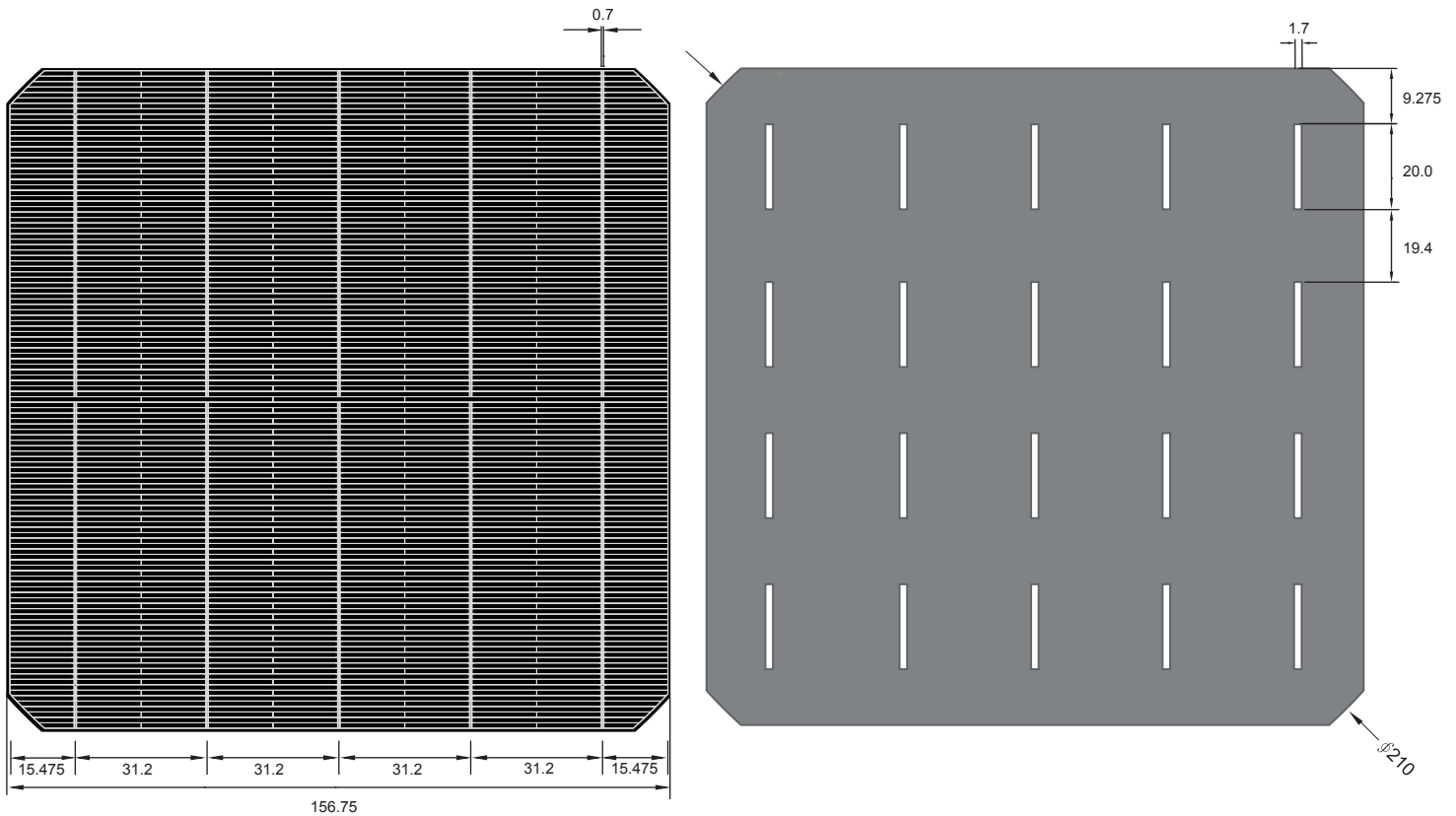




# Mono-crystalline Silicon 6" PERC Solar Cell

P6E5H



## Physical Characteristics

Cell type	Mono-crystalline Silicon PERC Solar Cell
Dimension	156.75 mm x 156.75 mm $\pm$ 0.25 mm 210 mm $\pm$ 0.25 mm (Diagonal length)
Cell Thickness	190 $\mu$ m $\pm$ 30 $\mu$ m
Front side (–)	Silicon nitride anti-reflection coating Five 0.7 $\pm$ 0.1 mm wide bus bars with distance 31.2 mm
Back side (+)	Full surface aluminum back surface field Five 1.7 $\pm$ 0.1 mm discontinuous soldering pads

# P6E5H

## General Characteristics

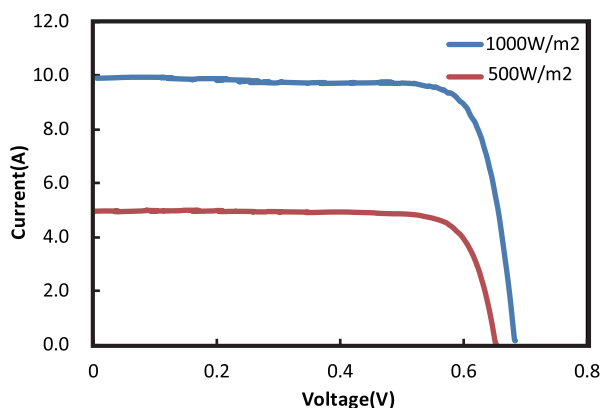
Eff(%)	Pmpp(Pmax)	Voc	Isc	Vmpp(Vmp)	Impp(Impp)
21.2	5.18	0.661	9.83	0.558	9.28
21.3	5.20	0.662	9.85	0.559	9.31
21.4	5.23	0.663	9.87	0.560	9.34
21.5	5.25	0.664	9.89	0.561	9.36
21.6	5.28	0.665	9.91	0.562	9.39
21.7	5.30	0.666	9.92	0.563	9.42
21.8	5.33	0.667	9.93	0.565	9.43
21.9	5.35	0.669	9.95	0.567	9.44
22.0	5.37	0.670	9.96	0.569	9.44
22.1	5.40	0.671	9.97	0.570	9.47
22.2	5.42	0.672	9.98	0.572	9.48
22.3	5.45	0.673	9.99	0.573	9.51
22.4	5.47	0.674	10.01	0.574	9.53

- Under standard test condition : 1000W / m<sup>2</sup> , AM 1.5 , 25°C • Illustration : 21.6% → actual range 21.6%~21.69%
- Specification and data are for reference only and may change without prior notice.

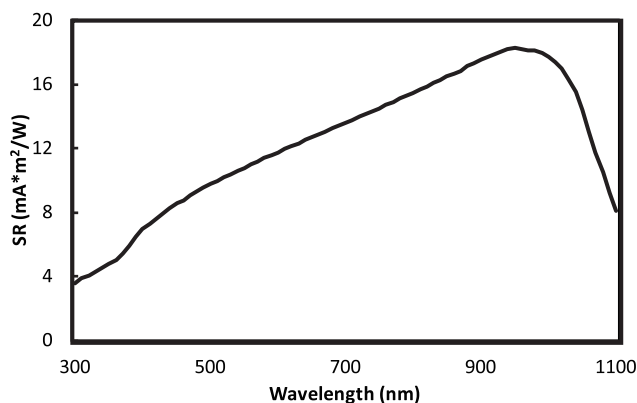
## Temperature coefficient

Voc	Isc	FF	Power
-0.2771%/K	0.0650%/K	-0.1123%/K	-0.3212%/K

## Typical I-V Curve



## Spectral Response



## Electrical Properties

Parameter	Grade A
Cell efficiency / P <sub>mp</sub>	Measured cell efficiency (or P <sub>mp</sub> ) according to above mentioned bin criteria (AM 1.5, 1000 W/m <sup>2</sup> , 25 °C)
Shunt Resistivity	> 30 Ohm
Reverse dark current	I <sub>rev 2</sub> < 1.5A at -12V and 25°C